L Number	Hits	Search Text	DB	Time stamp
-	2332	etch\$3 same (oxide sio2 "sio.sub.2" TEOS)	USPAT;	2003/09/15 09:58
		same (nitride SiN Si3N4 "Si.sub.3 N.sub.4")	US-PGPUB;	
		AND ((polymer polymeric) same deposit\$3)	EPO; JPO;	
		• •	DERWENT;	
			IBM_TDB	
-	686	etch\$3 same (oxide sio2 "sio.sub.2" TEOS)	USPAT;	2003/09/15 09:59
		same (nitride SiN Si3N4 "Si.sub.3 N.sub.4")	US-PGPUB;	
		same ((polymer polymeric) same deposit\$3)	EPO; JPO;	
			DERWENT;	
		_	IBM_TDB	
-	36		USPAT;	2003/09/15 10:59
		with (nitride SiN Si3N4 "Si.sub.3 N.sub.4")	US-PGPUB;	
		with (underlying overlying)) same ((polymer	EPO; JPO;	I
		polymeric) same deposit\$3)	DERWENT;	
			IBM_TDB	
-	20	(etch\$3 same ((oxide sio2 "sio.sub.2" TEOS)	USPAT;	2003/09/15 10:02
		with (nitride SiN Si3N4 "Si.sub.3 N.sub.4")	US-PGPUB;	
		with (underlying overlying)) same ((polymer	EPO; JPO;	
		polymeric) same deposit\$3)) and high adj	DERWENT;	
		density	IBM_TDB	
-	0		USPAT;	2003/09/15 10:02
		with (nitride SiN Si3N4 "Si.sub.3 N.sub.4")	US-PGPUB;	
		with (underlying overlying)) same ((polymer	EPO; JPO;	
		polymeric) same deposit\$3)) and high adj	DERWENT;	
		density) and ceiling with temperature	IBM_TDB	
-	0	((etch\$3 same ((oxide sio2 "sio.sub.2" TEOS)	USPAT;	2003/09/15 10:03
		with (nitride SiN Si3N4 "Si.sub.3 N.sub.4")	US-PGPUB;	
		with (underlying overlying)) same ((polymer	EPO; JPO;	
		polymeric) same deposit\$3)) and high adj	DERWENT;	
1		density) and ceiling with (heat\$3 cool\$3)	IBM_TDB	
-	0		USPAT;	2003/09/15 10:03
		with (nitride SiN Si3N4 "Si.sub.3 N.sub.4")	US-PGPUB;	
		with (underlying overlying)) same ((polymer	EPO; JPO;	
		polymeric) same deposit\$3)) and ceiling with	DERWENT;	
		(heat\$3 cool\$3 temperature)	IBM_TDB	
-	5		USPAT;	2003/09/15 10:04
		same (nitride SiN Si3N4 "Si.sub.3 N.sub.4")	US-PGPUB;	
		same ((polymer polymeric) same deposit\$3))	EPO; JPO;	
		and ceiling with (heat\$3 cool\$3 temperature)	DERWENT;	
			IBM_TDB	0000/00/05 10 00
-	26		USPAT;	2003/09/15 10:33
i		same (nitride SiN Si3N4 "Si.sub.3 N.sub.4")	US-PGPUB;	
		AND ((polymer polymeric) same deposit\$3))	EPO; JPO;	
		and ceiling with (heat\$3 cool\$3 temperature)	DERWENT;	
		(	IBM_TDB	2002/00/15 10:42
<del>-</del>	21	((etch\$3 same (oxide sio2 "sio.sub.2" TEOS)	USPAT;	2003/09/15 10:43
		same (nitride SiN Si3N4 "Si.sub.3 N.sub.4")	US-PGPUB;	
		AND ((polymer polymeric) same deposit\$3))	EPO; JPO;	
		and ceiling with (heat\$3 cool\$3	DERWENT;	
		temperature)) not ((etch\$3 same (oxide sio2	IBM_TDB	
1		"sio.sub.2" TEOS) same (nitride SiN Si3N4		
		"Si.sub.3 N.sub.4") same ((polymer		1
		polymeric) same deposit\$3)) and ceiling with		
		(heat\$3 cool\$3 temperature))	TIODATE -	2003/09/15 10:43
-	16		USPAT;	2003/03/13 10:43
		with (nitride SiN Si3N4 "Si.sub.3 N.sub.4")	US-PGPUB;	
		with (underlying overlying)) same ((polymer	EPO; JPO;	
		polymeric) same deposit\$3)) not ((etch\$3	DERWENT;	
		same ((oxide sio2 "sio.sub.2" TEOS) with	IBM_TDB	
		(nitride SiN Si3N4 "Si.sub.3 N.sub.4") with		
		(underlying overlying)) same ((polymer		
		polymeric) same deposit\$3)) and high adj		
	l	density)		

	40	((etch\$3 same ((oxide sio2 "sio.sub.2" TEOS)	USPAT;	2003/09/15 11:01
		with (nitride SiN Si3N4 "Si.sub.3 N.sub.4")	US-PGPUB;	
		with (underlying overlying)) same ((polymer	EPO; JPO;	
	ļ.	polymeric) same deposit\$3)) ((etch\$3 same	DERWENT;	
		(oxide sio2 "sio.sub.2" TEOS) same (nitride	IBM_TDB	
		SiN Si3N4 "Si.sub.3 N.sub.4") AND ((polymer		
		polymeric) same deposit\$3)) and ceiling with		
		(heat\$3 cool\$3 temperature))) and (CHF3 CF3H		
		CH2F2 CF2H2 "CHF.sub.3" "CF.sub.3 H"		
	1	"CH.sub.2 F.sub.2" "CF.sub.2 H.sub.2")		0000/00/15 11 01
-	9	(US-5801083-\$ or US-6180533-\$ or	USPAT	2003/09/15 11:01
		US-5477975-\$ or US-5722668-\$ or US-5865896-\$		
		or US-5990017-\$ or US-6296780-\$ or		
		US-6465051-\$ or US-5399237-\$).did.		
-	5	(((US-5801083-\$ or US-6180533-\$ or	USPAT;	2003/09/15 11:02
		US-5477975-\$ or US-5722668-\$ or US-5865896-\$	US-PGPUB;	
		or US-5990017-\$ or US-6296780-\$ or	EPO; JPO;	
		US-6465051-\$ or US-5399237-\$).did.)) and	DERWENT;	
		(CHF3 CF3H CH2F2 CF2H2 "CHF.sub.3" "CF.sub.3	IBM_TDB	
	ì	H" "CH.sub.2 F.sub.2" "CF.sub.2 H.sub.2")	1	
-	5	((((US-5801083-\$ or US-6180533-\$ or	USPAT;	2003/09/15 11:04
	1	US-5477975-\$ or US-5722668-\$ or US-5865896-\$	US-PGPUB;	
	1	or US-5990017-\$ or US-6296780-\$ or	EPO; JPO;	
		US-6465051-\$ or US-5399237-\$).did.)) and	DERWENT;	
	1	(CHF3 CF3H CH2F2 CF2H2 "CHF.sub.3" "CF.sub.3	IBM_TDB	
		H" "CH.sub.2 F.sub.2" "CF.sub.2 H.sub.2"))		
	,	and (ar he H2 "h.sub.2" argon helium		
		hydrogen)		
_	5	(((((US-5801083-\$ or US-6180533-\$ or	USPAT;	2003/09/15 11:04
		US-5477975-\$ or US-5722668-\$ or US-5865896-\$	US-PGPUB;	
		or US-5990017-\$ or US-6296780-\$ or	EPO; JPO;	
		US-6465051-\$ or US-5399237-\$).did.)) and	DERWENT;	
		(CHF3 CF3H CH2F2 CF2H2 "CHF.sub.3" "CF.sub.3	IBM_TDB	
		H" "CH.sub.2 F.sub.2" "CF.sub.2 H.sub.2"))		
		and (ar he H2 "h.sub.2" argon helium		
	1	hydrogen) ) and bias\$3		
-	17	US-4786359-\$.DID. OR US-0074456-\$.DID. OR	USPAT;	2003/09/16 13:49
	1	US-5770099-\$.DID. OR US-5880036-\$.DID. OR	US-PGPUB;	
		US-5888414-\$.DID. OR US-5990017-\$.DID. OR	EPO; JPO;	Į
		US-6036877-\$.DID. US-5779849-\$.DID. OR	DERWENT;	
		US-5599396-\$.DID.	IBM TDB	
_	11		USPAT;	2003/09/16 13:50
_	""	US-5556501-\$.DID. OR US-5770099-\$.DID. OR	US-PGPUB;	
		US-5477975-\$.DID. OR US-6077384-\$.DID.	EPO; JPO;	
		00 01,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	DERWENT;	
			IBM TDB	